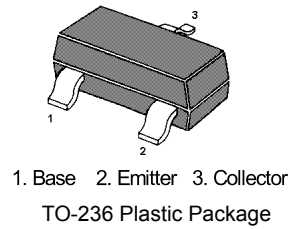
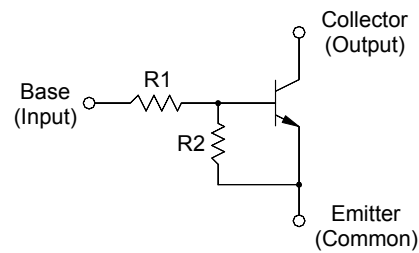


MMDT221F

NPN Silicon Epitaxial Planar Transistor

For digital circuits applications

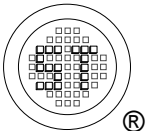


Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	50	V
Collector Current	I_C	100	mA
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}\text{C}$

Resistor Values

Type	R1 (K Ω)	R2 (K Ω)
MMDT221F	4.7	10



MMDT221F

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 10\text{ V}$, $I_C = 5\text{ mA}$	h_{FE}	30	-	-	-
Collector Base Cutoff Current at $V_{CB} = 50\text{ V}$	I_{CBO}	-	-	100	nA
Collector Emitter Cutoff Current at $V_{CE} = 50\text{ V}$	I_{CEO}	-	-	500	nA
Emitter Base Cutoff Current at $V_{EB} = 6\text{ V}$	I_{EBO}	-	-	1	mA
Collector Base Breakdown Voltage at $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	50	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 2\text{ mA}$	$V_{(BR)CEO}$	50	-	-	V
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 0.3\text{ mA}$	V_{CEsat}	-	-	0.25	V
Output Voltage Low Level at $V_{CC} = 5\text{ V}$, $V_B = 2.5\text{ V}$, $R_L = 1\text{ K}\Omega$	V_{OL}	-	-	0.2	V
Output Voltage High Level at $V_{CC} = 5\text{ V}$, $V_B = 0.5\text{ V}$, $R_L = 1\text{ K}\Omega$	V_{OH}	4.9	-	-	V
Transition Frequency at $V_{CB} = 10\text{ V}$, $-I_E = 2\text{ mA}$, $f = 200\text{ MHz}$	f_T	-	150	-	MHz
Input Resistor	R_1	3.3	4.7	6.1	$\text{K}\Omega$
Resistor Ratio	R_1 / R_2	0.37	-	0.57	-

